

GMP-5, GMP-5A, GMP-5B, e3 SERIES

TRANSIENT ABSORPTION ZENER

DESCRIPTION

The GMP-5 series is a low voltage Transient Voltage Suppressor designed for the protection of integrated circuits with very low Clamping Voltages (V_c). Due to their very fast response time, protection level and high discharge capability, they are extremely effective in providing protection against 5-volt line transients generated by: voltage reversals, capacitive or inductive load switching. electromechanical switching, electrostatic discharge and electromagnetic coupling.

APPEARANCE

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IMPORTANT: For the most current data, consult MICROSEMI's website: http://www.microsemi.com

FEATURES

- 500 Watts Peak Pulse Power dissipation. ٠
- Working Voltage of 5 volts
- Protects TTL, ECL, DTL, MOS, CMOS, and MSI Integrated circuits.
- Low clamping factor
- RoHS Compliant devices available by adding "e3" suffix

MAXIMUM RATINGS

- 500 Watts of Peak Pulse Power dissipation at ٠ 25°C.
- t_{clamping} (0 volts to BV min.): Less than 1x10-12 seconds (theoretical)
- Operating and Storage Temperatures: -65°C to +175°C.
- Forward surge rating: 50 amps 1/120 second at 25°C.
- Steady State power dissipation: 5.0 W @ T₁ = 75° C, Lead Length = $3/8^{\circ}$
- Repetition rate (duty cycle): .05%

The GMP-5 is a low voltage transient suppressor

designed for the protection of integrated circuits. Characterized by a very low clamping voltage together with a low standoff voltage, GMP-5's afford a high degree of protection to: TTL, ECL, DTL, MOS, CMOS, VMOS, HMOS, NMOS and static memory circuits susceptible to 5-volt line transients.

APPLICATIONS / BENEFITS



- CASE: Void free transfer molded thermosetting ٠ plastic.
- FINISH: Tin-lead or RoHS Compliant matte-Tin plating solderable per MIL-STD-750, method 2026
- POLARITY: Band denotes cathode.
- WEIGHT: 0.7 gram (approx.)
- MOUNTING POSITION: Any.

ELECTRICAL CHARACTERISTICS @ 25°C								
MICROSEMI PART NUMBER	STAND OFF VOLTAGE Note 1 V _{WM} Volts	MAXIMUM REVERSE LEAKAGE @V _{WM} Ι _D	MINIMUM BREAKDOWN VOLTAGE @ 1mA V (min) V _(BR) Volts	MAXIMUM CLAMPING VOLTAGE @ IPP1 = 1A (Fig. 2) Vc Volts	MAXIMUM CLAMPING VOLTAGE @ I _{PP2} = 1A (Fig. 2) V _C Volts	MAXIMUM PEAK PULSE CURRENT (Fig 2) IPP3 Amps	MAXIMUM PEAK PULSE CURRENT (1.2x50 µSeC) Amps	MP-5,5A,5
GMP – 5	5.0	300	5.3	6.7	6.9	70	215	ă
GMP – 5A	5.0	100	5.5	6.7	6.9	70	215	Ģ
GMP – 5B	5.0	300	5.3	6.4	6.6	70	215	G

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Vf at 50 amps peak, 8.3 msec sine wave = 3.5 volts maximum

NOTE 1: A TVS is usually selected according to the reverse "Stand Off Voltage" (V_{VMM}) which should be equal to or greater than the DC or continuous peak operating voltage level.

Microsemi Scottsdale Division

Page 1



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OUTLINE AND CIRCUIT 100 Peak Pulse Power (Ppp) in kW Π g Test wave form parameters pp - Peak Pulse Current - % Peak Value Ipp 0 tr = 10usec. tp = 1000µsec. Half Value Ipp Ħ П 2 (1000 Wave form 10 t - Time - msec 10us 100u 10ms 100ns 1us 1ms **FIGURE 2 Pulse Time** Pulse Wave Form **FIGURE 1** Peak Pulse Power vs. Pulse Time Ipp - Peak Pulse Current - Amps DIMENSIONS a æ 100% Peak Pulse Power (PPP) or Current (IPP) 1.06 (0.042) 40 DIA. TWO PLACES in percent of 25°C rating 75 20 8.89 (0.350) 8.39 (0.330) TYPICAL 10 . 50 6 25.4 (1.00) MIN. TWO PLACES 4 25 2 . 3.68 (0.145) 3.31 (0.130) 0 50 100 150 200 3 5 6 7 89% T - Temperature - °C Vc - Clamping Voltage - Volts **FIGURE 4 FIGURE 3 Derating Curve** Typical Characteristic Clamping Voltage (V_c) vs. Peak Pulse Current (I_{PP})

Page 2